L Number	Hits	Search Text	DB	Time stamp
- Humber	3	HSG and hemispherical and electrode and	USPAT;	2004/03/10 12:59
		(monolayer or monoatomiclayer or	EPO; JPO;	
		"mono-atomic layer" or "atomic layer") and	DERWENT	
		semiconductor		
_	0	HSG and hemispherical and electrode and	USPAT;	2001/03/21 14:58
		ALCVD	EPO; JPO;	
			DERWENT	
-	0	HSG and hemispherical and ALCVD	USPAT;	2001/03/21 14:58
			EPO; JPO;	
			DERWENT	
-	0	HSG and hemispherical and ALCVD	USPAT;	2001/03/21 14:58
			EPO; JPO;	
			DERWENT	
-	0	HSG and ALCVD	USPAT;	2001/03/21 14:58
			EPO; JPO;	
			DERWENT	2001/02/21 14 50
-	4	ALCVD	USPAT;	2001/03/21 14:59
			EPO; JPO;	
	0	USC and arring and (diplostic adil layor)	DERWENT USPAT;	2001/03/21 15:01
-	U	HSG and grain\$1 and (dielectic adj1 layer) and monolayer\$1	EPO; JPO;	2001/03/21 15:01
		and monorayerar	DERWENT	
_	o	HSG and grain\$1 and (dielectic adj1 layer)	USPAT;	2001/03/21 15:17
		and (atomic adj1 layer)	EPO; JPO;	2001,03,21 13:17
		and (acomic daji layor)	DERWENT	
_	691	HSG and hemispherical	USPAT;	2001/03/21 15:17
			EPO; JPO;	
			DERWENT	
-	224	(HSG and hemispherical) and nitride and	USPAT;	2001/03/21 15:18
		oxide and metal	EPO; JPO;	
			DERWENT	
-	34	((HSG and hemispherical) and nitride and	USPAT;	2001/03/21 15:18
		oxide and metal) and (multilayer or	EPO; JPO;	
		"multy-layer")	DERWENT	
-	48	((HSG and hemispherical) and nitride and	USPAT;	2001/03/21 15:37
		oxide and metal) and (multilayer or	EPO; JPO;	
		"multi-layer")	DERWENT	2001/03/21 15:38
-	0	HSG and ALD	USPAT;	2001/03/21 15:38
			EPO; JPO; DERWENT	
	758	ALD	USPAT;	2001/03/21 15:38
	, 50	THE STATE OF THE S	EPO; JPO;	=====================================
			DERWENT	
_	77	ALD and electrode\$1	USPAT;	2001/03/22 08:59
		·	EPO; JPO;	
			DERWENT	
-	3	(("5626906") or ("6124158") or	USPAT	2001/03/21 15:44
		("6090659")).PN.		
] -	77	ALD and electrode\$1	USPAT;	2001/03/22 09:11
			EPO; JPO;	
	_	("6000650") PX	DERWENT	2001/02/22 02 42
-	1	("6090659").PN.	USPAT;	2001/03/22 09:40 2001/03/22 09:41
-	U	HSG and grain\$1 and hemisperical and (high adj1 dielectric adj1 constant)	EPO; JPO;	2001/03/22 03:41
]		auji dielectic auji constant/	DERWENT	
<u>-</u>	o	HSG and hemisperical and (high adj1	USPAT;	2001/03/22 09:42
	ľ	dielectric adj1 constant)	EPO; JPO;	
			DERWENT	
-	1	HSG and hemisperical and (dielectric adj1	USPAT;	2001/03/22 09:43
	_	constant)	EPO; JPO;	
			DERWENT	
-	194	HSG and (dielectric adj1 constant)	USPAT;	2001/03/22 09:43
		_	EPO; JPO;	
			DERWENT	
-	126	HSG and (high adjl dielectric adjl constant)	USPAT;	2001/03/22 09:43
			EPO; JPO;	
	į		DERWENT	0000/00/00 00
] -	110		USPAT;	2001/03/22 09:43
		constant)) and electrode\$1	EPO; JPO;	
	<u> </u>		DERWENT	<u> </u>

-	307036	((HSG and (high adj1 dielectric adj1	USPAT;	2001/03/22 09:44
		constant)) and electrode\$1) ang grain\$1	EPO; JPO;	,
			DERWENT	
-	86	((HSG and (high adj1 dielectric adj1	USPAT;	2001/03/22 09:44
		constant)) and electrode\$1) and grain\$1	EPO; JPO;	
			DERWENT	
-	79	(((HSG and (high adj1 dielectric adj1	USPAT;	2001/03/22 14:49
		constant)) and electrode\$1) and grain\$1) and	EPO; JPO;	
		hemispherical	DERWENT	
-	15	WO93/12542	USPAT;	2001/03/22 14:49
			EPO; JPO;	
			DERWENT	
-	0	WO9312542	USPAT;	2001/03/22 14:50
		·	EPO; JPO;	
			DERWENT	
-	o	WO9312542.did.	USPAT;	2001/03/22 14:50
			EPO; JPO;	
	-		DERWENT	
_	0	W9312542.did.	USPAT;	2001/03/22 14:50
			EPO; JPO;	
			DERWENT	
_	o	WO9312542.did.	USPAT;	2001/03/22 14:51
<u> </u>			EPO; JPO;	,,
			DERWENT	
_	o	WO-9312542	USPAT;	2001/03/22 14:51
-		10-5312542	EPO; JPO;	2001,03,22 14.31
			DERWENT	
_	٦	9312542.did.	DERWENT	2001/03/22 14:51
-	411	9312542.d1d. (dielectric adjl layer) with (Si or silicon)	USPAT;	2001/03/22 14:51 2003/10/17 16:06
-	411			2003/10/17 16:06
		with (oxygen or oxide) with metal	EPO; JPO;	
		(41-7	DERWENT	2001/02/22 10 21
-	19	(dielectric adj1 layer) with (Si or silicon)	USPAT;	2001/03/23 10:24
		with (oxygen or oxide) with metal with CVD	EPO; JPO;	
			DERWENT	2002/25/22 25 25
-	14	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2003/06/10 15:27
		with k with dielectric))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	,
-	187	capacitor and ALD	USPAT;	2003/10/17 16:06
			EPO; JPO;	
			DERWENT	
-	15	(capacitor and ALD) and HSG	USPAT;	2003/10/17 16:37
			EPO; JPO;	
į			DERWENT	
-	13	semiconductor and ALD.ti.	USPAT;	2003/10/17 16:38
			EPO; JPO;	
1			DERWENT	
_	5	(semiconductor and ALD.ti.) and purge	USPAT;	2003/10/17 16:37
			EPO; JPO;	
			DERWENT	
_	5	((semiconductor and ALD.ti.) and purge) and	USPAT;	2003/10/17 16:37
		aluminum	EPO; JPO;	' '
			DERWENT	j l
_	33	ALD.ti.	USPAT;	2003/10/17 16:38
			EPO; JPO;	,,
			DERWENT	
_	28	ALD.ti. not (((semiconductor and ALD.ti.)	USPAT;	2003/10/17 16:39
·	20	and purge) and aluminum)	EPO; JPO;	
		and purge, and araminam,	DERWENT	
	48	ALD and (PZT or BST)	USPAT;	2003/10/20 14:03
-	40	AND AND LEAT OF BOIL	EPO; JPO;	2003/10/20 14.03
			DERWENT	
	28	(ALD and (PZT or BST)) and capacitor	USPAT;	2003/10/20 14:04
-	28	Ann and fer or poll! and capacitor	·	2003/10/20 14:04
			EPO; JPO;	
1	_	(MaO on /bontalism add masterida)	DERWENT	2004/02/00 30 40
-	5		USPAT;	2004/03/09 19:49
		(tantalum adj oxide) or "TaO.sub.5") and ALD	EPO; JPO;]
		and HSG	DERWENT	0004/00/00 10 70
-	4	(high with k with dielectric) and ALD and	USPAT;	2004/03/09 19:50
		HSG	EPO; JPO;	
	<u> </u>	49.44	DERWENT	<u> </u>

			Litonia	10004/00/00 10 51
-	70	(high with k with dielectric) and ALD	USPAT; EPO; JPO;	2004/03/09 19:51
-	30	((high with k with dielectric) and ALD) and monolayer\$1	DERWENT USPAT; EPO; JPO; DERWENT	2004/03/09 19:56
-	1	HSG and (high with k) same (silicon same oxygen same metal)	USPAT; EPO; JPO; DERWENT	2004/03/09 19:58
-	1	HSG and (high with k) same (si same oxygen same metal)	USPAT; EPO; JPO;	2004/03/09 19:58
_	1	HSG and (high with k) same (si same metal same oxide)	DERWENT USPAT; EPO; JPO; DERWENT	2004/03/09 20:06
-	3	HSG and (high with k) same (MIS)	USPAT; EPO; JPO;	2004/03/09 20:07
-	6	HSG and (high with k) same (MIM\$1)	DERWENT USPAT; EPO; JPO;	2004/03/09 20:07
_	57	HSG and (MIM\$1 or MIS)	DERWENT USPAT; EPO; JPO;	2004/03/09 20:16
-	19	US-6521943-\$ or US-6489214-\$ or US-6387761-\$	DERWENT USPAT	2004/03/09 20:15
		or US-6372598-\$ or US-6335240-\$ or US-6281142-\$ or US-6204203-\$ or US-6159793-\$ or US-6144062-\$ or US-6074913-\$ or US-6057205-\$ or US-6037235-\$ or US-5998264-\$ or US-5994197-\$ or US-5726085-\$ or US-5723373-\$ or US-6589839-\$).did.		
	0	((US-5463235-\$ or US-5444653-\$ or US-6521943-\$ or US-6489214-\$ or US-6387761-\$ or US-6372598-\$ or US-6335240-\$ or US-6281142-\$ or US-6204203-\$ or US-6159793-\$ or US-6144062-\$ or US-6074913-\$ or US-6057205-\$ or US-6037235-\$ or US-5998264-\$ or US-5994197-\$ or US-5726085-\$ or US-5723373-\$ or US-6589839-\$).did.) and monolayer\$1	USPAT; EPO; JPO; DERWENT	2004/03/09 20:16
-	2	((US-5463235-\$ or US-5444653-\$ or US-6521943-\$ or US-6489214-\$ or US-6387761-\$ or US-6372598-\$ or US-6335240-\$ or US-6281142-\$ or US-6204203-\$ or US-6159793-\$ or US-6144062-\$ or US-6074913-\$ or US-6057205-\$ or US-6037235-\$ or US-5998264-\$ or US-5994197-\$ or US-5726085-\$ or	USPAT; EPO; JPO; DERWENT	2004/03/09 20:16
	2	US-5723373-\$ or US-6589839-\$).did.) and ALD ((US-5463235-\$ or US-5444653-\$ or US-6521943-\$ or US-6489214-\$ or US-6387761-\$ or US-6372598-\$ or US-6335240-\$ or US-6281142-\$ or US-6204203-\$ or US-6159793-\$ or US-6144062-\$ or US-6074913-\$ or US-6057205-\$ or US-6037235-\$ or US-5998264-\$ or US-5994197-\$ or US-5726085-\$ or US-5723373-\$ or US-6589839-\$).did.) and (ALD or (atomic adillayer))	USPAT; EPO; JPO; DERWENT	2004/03/09 20:16
-	0	or (atomic adj layer)) ALD and (metal adj ethoxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 12:59
-	32	ALD and (ethoxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:02
-	296	monolayer\$1 and (ethoxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:04
-	1	(monolayer\$1 and (ethoxide)) and HSG	USPAT; EPO; JPO; DERWENT	2004/03/10 13:03

-	0	(HSG or (hemispherical adj grain)) and	USPAT;	2004/03/10 13:05
		(metal adj siloxane)	EPO; JPO; DERWENT	
-	0	(HSG or (hemispherical adj grain)) and (silicon adj metiloxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:05
-	0	(HSG or (hemispherical adj grain)) and (silicon adj metaloxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:05
-	0	(HSG or (hemispherical adj grain)) and (silicon adj metal adj oxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 16:03